

**INVENTOR'S DECLARATION FOR
PATENT APPLICATION**

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name;

I believe I am the original, first and sole inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled

SOI MOSFET WITH MULTI-SIDED SOURCE/DRAIN SILICIDE

the specification of which: (check one)

_____ is attached hereto.

_____ was filed on
under Attorney's Docket Number
as Application Serial No.
and was amended on _____ (if applicable).

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to the patentability of this application in accordance with 37 CFR 1.56, including for continuation-in-part applications, material information which became available between the filing date of the prior application and the national or PCT international filing date of the continuation-in-part application.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

FULL NAME OF INVENTOR: Chun-Chieh Lin

INVENTOR'S SIGNATURE: _____ DATED: _____

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	§	Attorney Docket No.: 24061.151
Chun-Chieh Lin	§	TSMC2003-1013
	§	
Serial No. Unknown	§	Customer No. 27683
	§	
Filed: Herewith	§	Group Art Unit: Unknown
	§	
For: SOI MOSFET WITH MULTI-SIDED	§	Examiner: Unknown
SOURCE/DRAIN SILICIDE	§	

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

POWER OF ATTORNEY FOR PATENT APPLICATION

As a representative of the Assignee, Taiwan Semiconductor Manufacturing Company, Ltd., I hereby appoint the following attorneys and/or agents to prosecute this application and transact all business in the Patent and Trademark Office connected therewith.

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The undersigned is the representative for the Assignee of the entire right, title, and interest in the patent application identified above. A copy of the assignment or other documents in the chain of title are attached.

The undersigned (whose title is supplied below) is authorized to act on behalf of the Assignee.

Taiwan Semiconductor Manufacturing Company, Ltd.

Date

Chien-Wei Chou
Title: Director, IP Division